

**PRECURSORY RAW MATERIAL MIXTURE, FILM DEPOSITION METHOD AND FORMATION OF STRUCTURE**

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**Abstract**

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**PROBLEM TO BE SOLVED:** To provide a precursory raw material mixture useful for CVD and ALD, to provide a method for growing a film by using the same and to provide a method for forming an electronic device having the same film incorporated therein.

**SOLUTION:** At least one precursory compound containing a metallic element such as Li contains at least one precursory material inclusive of a compound such as a hydride, and the same is dissolved, emulsified or floated into an inert solution of aliphatic hydrocarbon or the like. The precursory raw material mixture is a solution, an emulsion or a suspension and is composed of a mixture of a solid phase, a liquid phase and a vapor phase, and they are dispersed over the whole mixture.

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